# 1. General description

NPN/PNP general-purpose transistor pair in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: BC846BS PNP/PNP complement: BC856BS

## 2. Features and benefits

- Low collector capacitance
- Low collector-emitter saturation voltage
- · Closely matched current gain
- · Reduces number of components and board space
- No mutual interference between the transistors

# 3. Applications

· General-purpose switching and amplification

## 4. Quick reference data

#### Table 1. Quick reference data

| Symbol           | Parameter   | Conditions  |  | Min | Тур | Max | Unit |  |  |
|------------------|---|---|--|-----|-----|-----|------|--|--|
| Per transistor;  | Per transistor; for the PNP transistor with negative polarity |   |  |     |     |     |      |  |  |
| V <sub>CEO</sub> | collector-emitter voltage                                     | open base   |  | -   | -   | 65  | V    |  |  |
| I <sub>C</sub>   | collector current   |   |  | -   | -   | 100 | mA   |  |  |
| TR1 (NPN)        | TR1 (NPN)   |   |  |     |     |     |      |  |  |
| h <sub>FE</sub>  | DC current gain   | $V_{CE}$ = 5 V; $I_{C}$ = 2 mA; $T_{amb}$ = 25 °C   |  | 200 | 300 | 450 |      |  |  |
| TR2 (PNP)        |   |   |  |     |     |     |      |  |  |
| h <sub>FE</sub>  | DC current gain   | $V_{CE}$ = -5 V; $I_{C}$ = -2 mA; $T_{amb}$ = 25 °C |  | 200 | 290 | 450 |      |  |  |



### 65 V, 100 mA NPN/PNP general-purpose transistor

# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description   | Simplified outline | Graphic symbol |
|-----|--------|---------------|--------------------|----------------|
| 1   | E1     | emitter TR1   |                    | C1 B2 E2       |
| 2   | B1     | base TR1      |                    |                |
| 3   | C2     | collector TR2 |                    | (TR1 TR2)      |
| 4   | E2     | emitter TR2   |                    |                |
| 5   | B2     | base TR2      | ☐1 ☐2 ☐3           |                |
| 6   | C1     | collector TR1 | TSSOP6 (SOT363)    | sym019         |

# 6. Ordering information

#### **Table 3. Ordering information**

| Type number | Package |   |               |  |  |  |
|-------------|---------|---|---------------|--|--|--|
|             | Name    | Description   | Version       |  |  |  |
| BC846BPN    |         | plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body | <u>SOT363</u> |  |  |  |

## 7. Marking

#### Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| BC846BPN    | PJ%             |

<sup>[1] % =</sup> placeholder for manufacturing site code

# 8. Limiting values

### Table 5. Limiting values

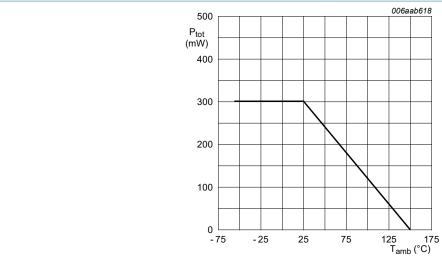
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                      | Conditions                          |     | Min | Max | Unit |
|------------------|--------------------------------|-------------------------------------|-----|-----|-----|------|
| Per transisto    | or; for the PNP transistor wit | h negative polarity                 | '   | '   | '   | '    |
| V <sub>CBO</sub> | collector-base voltage         | open emitter                        |     | -   | 80  | V    |
| $V_{CEO}$        | collector-emitter voltage      | open base                           |     | -   | 65  | V    |
| V <sub>EBO</sub> | emitter-base voltage           | open collector                      |     | -   | 6   | V    |
| I <sub>C</sub>   | collector current              |                                     |     | -   | 100 | mA   |
| I <sub>CM</sub>  | peak collector current         | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | 200 | mA   |
| I <sub>BM</sub>  | peak base current              |                                     |     | -   | 200 | mA   |
| P <sub>tot</sub> | total power dissipation        | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 200 | mW   |
| Per device       |                                |                                     | •   |     |     |      |
| P <sub>tot</sub> | total power dissipation        | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 300 | mW   |
| Tj               | junction temperature           |                                     |     | -   | 150 | °C   |
| T <sub>amb</sub> | ambient temperature            |                                     |     | -55 | 150 | °C   |
| T <sub>stg</sub> | storage temperature            |                                     |     | -65 | 150 | °C   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

BC846BPN

#### 65 V, 100 mA NPN/PNP general-purpose transistor



FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

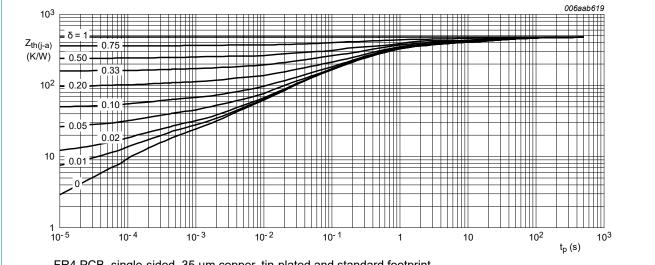
Fig. 1. Per device: Power derating curve

### Thermal characteristics

Table 6. Thermal characteristics

| Table 0. Them         | ilai Cilai acteristics                           |             |     | ,   |     |     |      |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| Symbol                | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
| Per transistor        | 1  |             |     |     |     |     |      |
| $R_{th(j-a)}$         | thermal resistance from junction to ambient      | in free air | [1] | -   | -   | 625 | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |             |     | -   | -   | 230 | K/W  |
| Per device            |  |             |     |     |     |     | '    |
| $R_{th(j-a)}$         | thermal resistance from junction to ambient      | in free air | [1] | -   | -   | 416 | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

Table 7. Characteristics

| Symbol             | Parameter                    | Conditions   | Min  | Тур  | Max  | Unit |
|--------------------|------------------------------|--|------|------|------|------|
| TR1 (NPN)          |                              |  |      |      |      |      |
| I <sub>CBO</sub>   | collector-base cut-off       | V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C   | -    | -    | 15   | nA   |
|                    | current                      | V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C  | -    | -    | 5    | μA   |
| I <sub>EBO</sub>   | emitter-base cut-off current | V <sub>EB</sub> = 6 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C  | -    | -    | 100  | nA   |
| h <sub>FE</sub>    | DC current gain              | V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 μA; T <sub>amb</sub> = 25 °C  | -    | 280  | -    |      |
|                    |                              | V <sub>CE</sub> = 5 V; I <sub>C</sub> = 2 mA; T <sub>amb</sub> = 25 °C   | 200  | 300  | 450  |      |
| V <sub>CEsat</sub> | collector-emitter            | I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA; T <sub>amb</sub> = 25 °C  | -    | 55   | 100  | mV   |
|                    | saturation voltage           | I <sub>C</sub> = 100 mA; I <sub>B</sub> = 5 mA; T <sub>amb</sub> = 25 °C   | -    | 200  | 300  | mV   |
| V <sub>BEsat</sub> | base-emitter saturation      | I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA; T <sub>amb</sub> = 25 °C  | -    | 755  | 850  | mV   |
|                    | voltage                      | I <sub>C</sub> = 100 mA; I <sub>B</sub> = 5 mA; T <sub>amb</sub> = 25 °C   | -    | 1000 | -    | mV   |
| V <sub>BE</sub>    | base-emitter voltage         | V <sub>CE</sub> = 5 V; I <sub>C</sub> = 2 mA; T <sub>amb</sub> = 25 °C   | 580  | 650  | 700  | mV   |
|                    |                              | V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C  | -    | -    | 770  | mV   |
| C <sub>c</sub>     | collector capacitance        | V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz;<br>T <sub>amb</sub> = 25 °C   | -    | 1.9  | -    | pF   |
| C <sub>e</sub>     | emitter capacitance          | V <sub>EB</sub> = 0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C  | -    | 11   | -    | pF   |
| f <sub>T</sub>     | transition frequency         | V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; f = 100 MHz;<br>T <sub>amb</sub> = 25 °C  | 100  | -    | -    | MHz  |
| NF                 | noise figure                 | $V_{CE} = 5 \text{ V; } I_{C} = 0.2 \text{ mA; } R_{S} = 2 \text{ k}\Omega;$<br>f = 15.7 kHz; $T_{amb} = 25 ^{\circ}\text{C}$                      | -    | 1.9  | -    | dB   |
|                    |                              | $V_{CE} = 5 \text{ V; } I_{C} = 0.2 \text{ mA; } R_{S} = 2 \text{ k}\Omega;$<br>$f = 1 \text{ kHz; } B = 200 \text{ Hz; } T_{amb} = 25 \text{ °C}$ | -    | 3.1  | -    | dB   |
| TR2 (PNP)          |                              |  |      |      |      |      |
| I <sub>CBO</sub>   | collector-base cut-off       | V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C  | -    | -    | -15  | nA   |
|                    | current                      | V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>i</sub> = 150 °C   | -    | -    | -5   | nA   |
| I <sub>EBO</sub>   | emitter-base cut-off current | V <sub>EB</sub> = -6 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C   | -    | -    | -100 | nA   |
| h <sub>FE</sub>    | DC current gain              | V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 μA; T <sub>amb</sub> = 25 °C  | -    | 270  | -    |      |
|                    |                              | V <sub>CE</sub> = -5 V; I <sub>C</sub> = -2 mA; T <sub>amb</sub> = 25 °C   | 200  | 290  | 450  | +    |
| V <sub>CEsat</sub> | collector-emitter            | I <sub>C</sub> = -10 mA; I <sub>B</sub> = -0.5 mA; T <sub>amb</sub> = 25 °C  | -    | -55  | -100 | mV   |
| 02041              | saturation voltage           | I <sub>C</sub> = -100 mA; I <sub>B</sub> = -5 mA; T <sub>amb</sub> = 25 °C   | -    | -200 | -300 | mV   |
| V <sub>BEsat</sub> | base-emitter saturation      | I <sub>C</sub> = -10 mA; I <sub>B</sub> = -0.5 mA; T <sub>amb</sub> = 25 °C  | -    | -755 | -850 | mV   |
| <del></del>        | voltage                      | I <sub>C</sub> = -100 mA; I <sub>B</sub> = -5 mA; T <sub>amb</sub> = 25 °C   | -    | -900 | -    | mV   |
| V <sub>BE</sub>    | base-emitter voltage         | V <sub>CE</sub> = -5 V; I <sub>C</sub> = -2 mA; T <sub>amb</sub> = 25 °C   | -600 | -650 | -750 | mV   |
|                    |                              | V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 mA; T <sub>amb</sub> = 25 °C  | -    | -    | -820 | mV   |
| C <sub>c</sub>     | collector capacitance        | V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C  | -    | 2.3  | -    | pF   |
| C <sub>e</sub>     | emitter capacitance          | V <sub>EB</sub> = -0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C                                       | -    | 10   | -    | pF   |
| f <sub>T</sub>     | transition frequency         | V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 mA; f = 100 MHz;<br>T <sub>i</sub> = 25 °C  | 100  | -    | -    | MHz  |

#### 65 V, 100 mA NPN/PNP general-purpose transistor

| Symbol | Parameter | Conditions  | Min | Тур | Max | Unit |
|--------|-----------|---|-----|-----|-----|------|
| NF     | , ,       | $V_{CE}$ = -5 V; $I_{C}$ = -0.2 mA; $R_{S}$ = 2 k $\Omega$ ;<br>f = 15.7 kHz; $T_{amb}$ = 25 °C       | -   | 1.6 | -   | dB   |
|        |           | $V_{CE}$ = -5 V; $I_{C}$ = -0.2 mA; $R_{S}$ = 2 k $\Omega$ ; f = 1 kHz; B = 200 Hz; $T_{amb}$ = 25 °C | -   | 2.9 | -   | dB   |

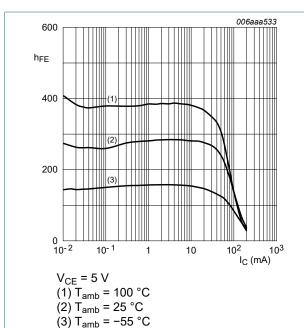
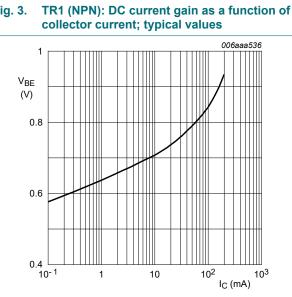
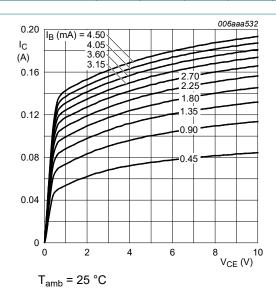


Fig. 3.

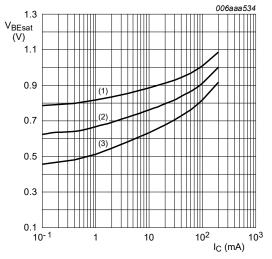


 $V_{CE}$  = 5 V;  $T_{amb}$  = 25 °C

TR1 (NPN): Base-emitter voltage as a function Fig. 5. of collector current; typical values



TR1 (NPN): Collector current as a function of Fig. 4. collector-emitter voltage; typical values



 $I_C/I_B = 20$ 

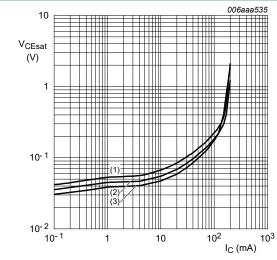
(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb}$  = 100 °C

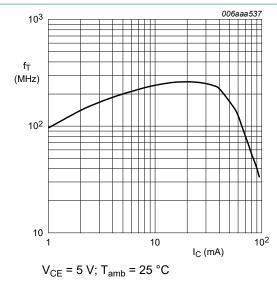
TR1 (NPN): Base-emitter saturation voltage as a Fig. 6. function of collector current; typical values

#### 65 V, 100 mA NPN/PNP general-purpose transistor



I<sub>C</sub>/I<sub>B</sub> = 20 (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -55 °C

TR1 (NPN): Collector-emitter saturation voltage Fig. 7. as a function of collector current; typical values



TR1 (NPN): Transition frequency as a function Fig. 8. of collector current; typical values

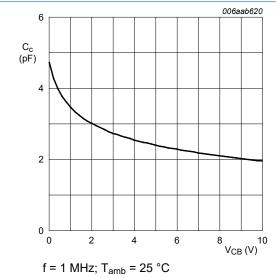


Fig. 9. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values

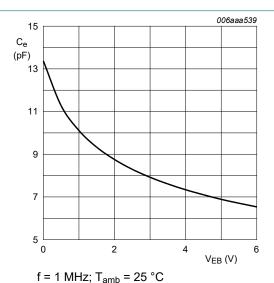


Fig. 10. TR1 (NPN): Emitter capacitance as a function of emitter-base voltage; typical values

#### 65 V, 100 mA NPN/PNP general-purpose transistor

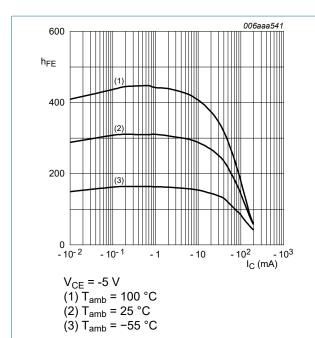


Fig. 11. TR2 (PNP): DC current gain as a function of collector current; typical values

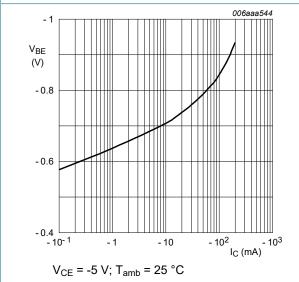


Fig. 13. TR2 (PNP): Base-emitter voltage as a function of collector current; typical values

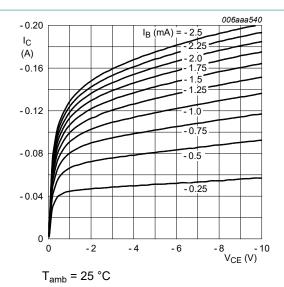
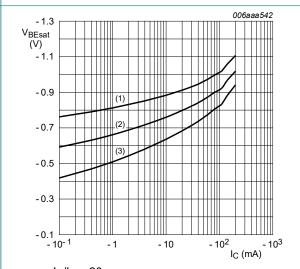


Fig. 12. TR2 (PNP): Collector current as a function of collector-emitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1)  $T_{\rm amb} = -55~{\rm ^{\circ}C}$ (2)  $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3)  $T_{\rm amb} = 100~{\rm ^{\circ}C}$ 

Fig. 14. TR2 (PNP): Base-emitter saturation voltage as a function of collector current; typical values

#### 65 V, 100 mA NPN/PNP general-purpose transistor

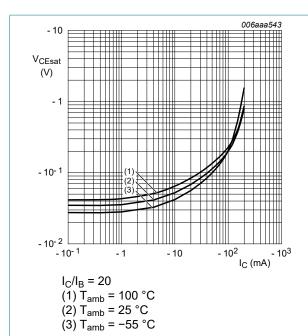


Fig. 15. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

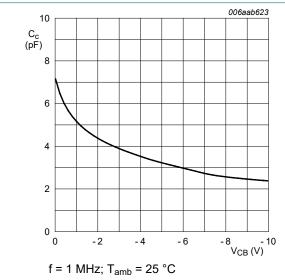


Fig. 17. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values

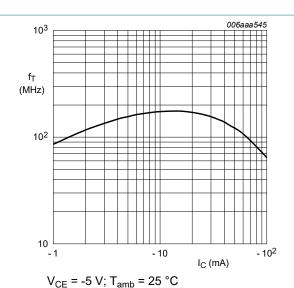


Fig. 16. TR2 (PNP): Transition frequency as a function of collector current; typical values

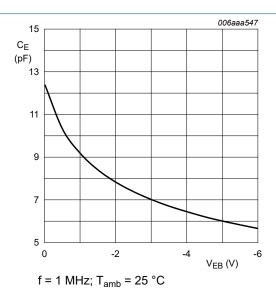
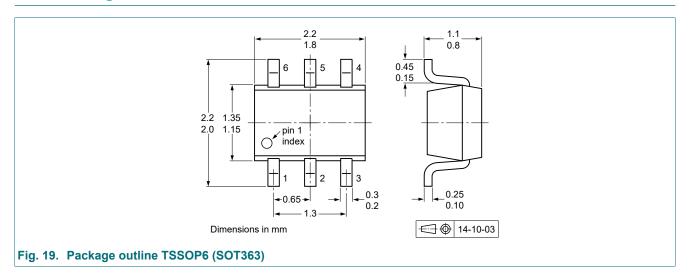


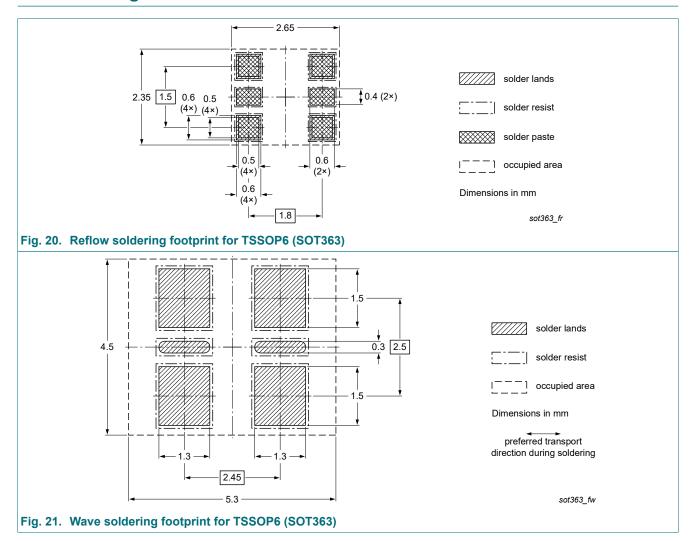
Fig. 18. TR2 (PNP): Emitter capacitance as a function of emitter-base voltage; typical values

#### 65 V, 100 mA NPN/PNP general-purpose transistor

# 11. Package outline



# 12. Soldering



## 65 V, 100 mA NPN/PNP general-purpose transistor

# 13. Revision history

#### **Table 8. Revision history**

| Data sheet ID  | Release date   | Data sheet status  | Change notice | Supersedes   |  |
|----------------|--|--------------------|---------------|--------------|--|
| BC846BPN v.2   | 20221001   | Product data sheet | -             | BC846BPN v.1 |  |
| Modifications: | <ul> <li>Product changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s).</li> <li>Packing information is removed.</li> </ul> |                    |               |              |  |
| BC846BPN v.1   | 20090717   | Product data sheet | -             | -            |  |

## 14. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <a href="https://www.nexperia.com">https://www.nexperia.com</a>.

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#### 65 V, 100 mA NPN/PNP general-purpose transistor

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### 65 V, 100 mA NPN/PNP general-purpose transistor

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